2.5V Drive Nch+SBD MOSFET **US5U3**

Structure

Silicon N-channel MOSFET/ Schottky barrier diode

● Features

- 1) Nch MOSFET and schottky barrier diode are put in TUMT5 package.
- 2) High-speed switching, Low On-resistance.
- 3) Low voltage drive (2.5V drive).
- 4) Built-in Low VF schottky barrier diode.

Applications

Switching

Package specifications

	Package	Taping	
Type	Code	TR	
	Basic ordering unit (pieces)	3000	
US5U3		0	

● Absolute maximum ratings (Ta=25°C)

<mosfet></mosfet>				
Parameter	Symbol	Limits	Unit	
Drain-source voltage		V _{DSS}	30	V
Gate-source voltage		V _{GSS}	12	V
Drain current	Continuous	ID	±1.5	Α
Drain current	Pulsed	IDP *1	±6.0	Α
Source current	Continuous	Is	0.6	A
(Body diode)	Pulsed	I _{SP} *1	6.0	A
Power dissipation		P _D *2	0.7	W/ELEMENT
Channel temperature		Tch	150	°C

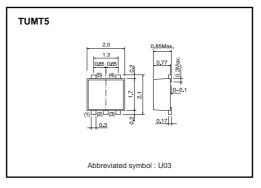
^{*1} Pw≤10µs, Duty cycle≤1% *2 Mounted on a ceramic board

<Di>

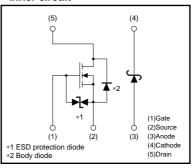
Parameter	Symbol	Limits	Unit
Repetitive peak reverse voltage	V _{RM}	25	V
Reverse voltage	V _R	20	V
Forward current	lF	0.7	A
Forward current surge peak	I _{FSM} *1	3.0	A
Power dissipation	P _D *2	0.5	W / ELEMENT
Junction temperature	Tj	150	°C

^{*1 60}Hz • 1cycle *2 Mounted on ceramic board

●Dimensions (Unit:mm)



•Inner circuit



<MOSFET and Di>

Parameter	Symbol	Limits	Unit	
Total power dissipation	P _D *1	1.0	W / TOTAL	
Range of storage temperature	Tstg	-55 to +150	°C	

^{*1} Mounted on a ceramic board

●Electrical characteristics (Ta=25°C)

<MOSFET>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	_	_	10	μΑ	V _{GS} =12V, V _{DS} =0V
Drain-source breakdown voltage	V(BR) DSS	30	_	_	٧	ID= 1mA, VGS=0V
Zero gate voltage drain current	IDSS	_	_	1	μΑ	V _{DS} = 30V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	0.5	_	1.5	V	V _{DS} = 10V, I _D = 1mA
Otation Indiana.		_	170	240	mΩ	I _D = 1.5A, V _{GS} = 4.5V
Static drain-source on-state resistance	RDS (on)*	1	180	250	mΩ	ID= 1.5A, VGS= 4V
- I esistance		-	240	340	mΩ	I _D = 1.5A, V _{GS} = 2.5V
Forward transfer admittance	Y _{fs} *	1.5	-	_	S	V _{DS} = 10V, I _D = 1.5A
Input capacitance	Ciss	_	80	_	pF	V _{DS} = 10V
Output capacitance	Coss	_	14	_	pF	V _{GS} =0V
Reverse transfer capacitance	Crss	-	12	-	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	_	7	_	ns	V _{DD} ≒ 15V
Rise time	tr *	_	9	_	ns	I _D = 0.75A V _G s= 4.5V
Turn-off delay time	t _{d (off)} *	_	15	_	ns	$R_{I} = 20\Omega$
Fall time	t _f *	_	6	_	ns	R _G =10Ω
Total gate charge	Qg *	_	1.6	2.2	nC	V _{DD} = 15V, V _{GS} = 4.5V
Gate-source charge	Q _{gs} *	-	0.5	-	nC	I _D = 1.5A
Gate-drain charge	Q _{gd} *	-	0.3	_	nC	$R_L=10\Omega$, $R_G=10\Omega$

^{*}Pulsed

<Body diode characteristics (Souce-drain)>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd	-	-	1.2	>	I _S = 0.6A, V _{GS} =0V

<Di>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	VF	-	_	0.49	V	IF= 0.7A
Reverse current	lr	_	_	200	μΑ	V _R = 20V

Electrical characteristics curves

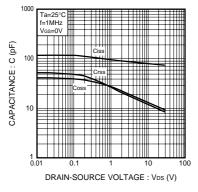


Fig.1 Typical Capacitance vs. Drain-Source Voltage

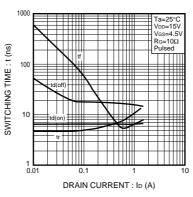


Fig.2 Switching Characteristics

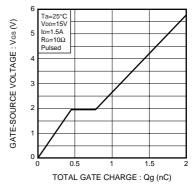


Fig.3 Dynamic Input Characteristics

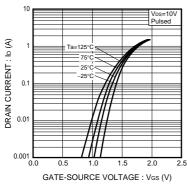


Fig.4 Typical Transfer Characteristics

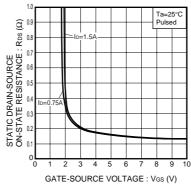


Fig.5 Static Drain-Source On-State Resistance vs. Gate source Voltage

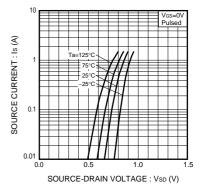


Fig.6 Source Current vs. Source-Drain Voltage

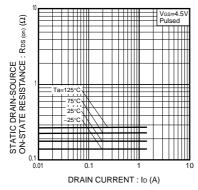


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (I)

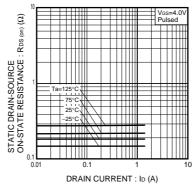


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current (II)

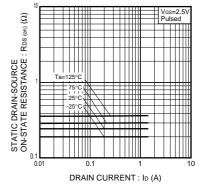


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current (III)

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